

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_A = 25^\circ\text{C}$
20V	$18.5\text{m}\Omega @ V_{GS} = 10\text{V}$	5.4 A
	$21\text{m}\Omega @ V_{GS} = 4.5\text{V}$	5.0 A
	$24\text{m}\Omega @ V_{GS} = 2.5\text{V}$	4.6 A
	$31\text{m}\Omega @ V_{GS} = 1.8\text{V}$	3.5 A

## Description

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

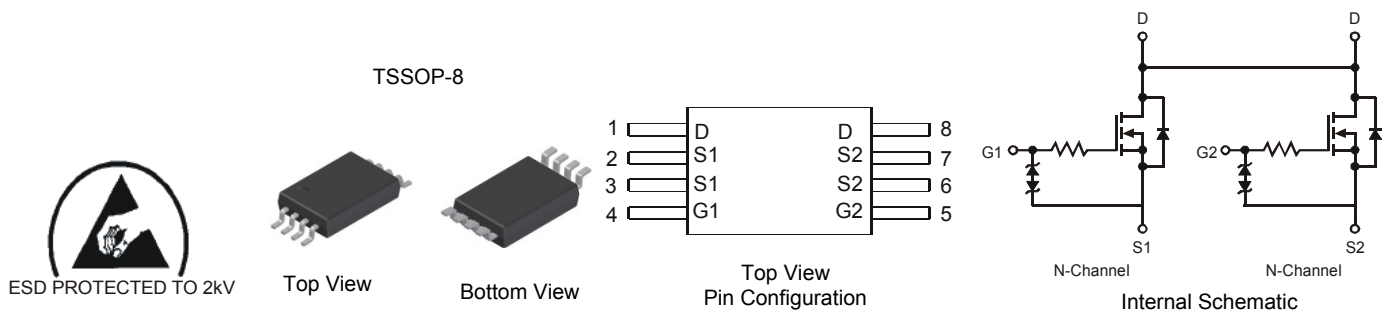
- Power management functions
- Load Switch

## Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected up to 2KV**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 standards for High Reliability**

## Mechanical Data

- Case: TSSOP-8
- Case Material: Molded Plastic, "Green" Molding Compound.  
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.039 grams (approximate)

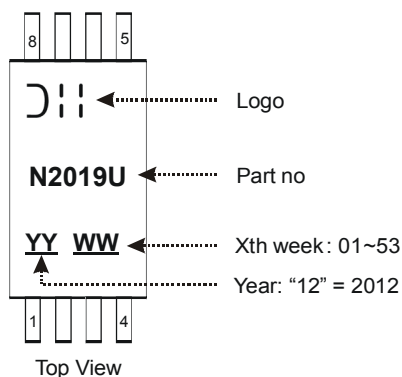


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2019UTS-13	TSSOP-8	2500/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  - See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information



**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic				Symbol	Value	Units
Drain-Source Voltage				V <sub>DSS</sub>	20	V
Gate-Source Voltage				V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 5)	V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	5.4	A
			T <sub>A</sub> = +70°C		4.3	
Continuous Drain Current (Note 5)	V <sub>GS</sub> = 2.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	4.6	A
			T <sub>A</sub> = +70°C		3.7	
Continuous Body Diode Forward Current (Note 5)		Steady Stat	T <sub>A</sub> = +25°C	I <sub>S</sub>	0.9	A
Pulsed Drain Current (Note 5) 10μs pulse, duty cycle = 1%				I <sub>DM</sub>	30	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	0.78	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	161	°C/W
Thermal Resistance, Junction to Case (Note 5)	R <sub>θJC</sub>	26	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1.0	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	10	μA	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V
Gate-Source Breakdown Voltage	BV <sub>SGS</sub>	±12	-	-	V	V <sub>DS</sub> = 0V, I <sub>G</sub> = ±250μA
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.35	-	0.95	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	-	15.5	18.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 7A
		-	16.5	21		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7A
		-	17	21.5		V <sub>GS</sub> = 4.0V, I <sub>D</sub> = 7A
		-	17.5	22.5		V <sub>GS</sub> = 3.6V, I <sub>D</sub> = 6.5A
		-	18	23		V <sub>GS</sub> = 3.1V, I <sub>D</sub> = 6.5A
		-	19	24		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 5.5A
		-	24	31		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 3.5A
		-	-	-		-
Forward Transfer Admittance	Y <sub>fs</sub>	-	13	-	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 5A
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	-	143	-	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	-	74	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	29	-	pF	
Gate Resistance	R <sub>g</sub>	-	202	-	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	-	8.8	-	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 6.5A
Gate-Source Charge	Q <sub>gs</sub>	-	1.4	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>	-	3.0	-	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	-	53	-	ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V, R <sub>L</sub> = 10Ω, R <sub>G</sub> = 6Ω
Turn-On Rise Time	t <sub>r</sub>	-	78	-	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	562	-	ns	
Turn-Off Fall Time	t <sub>f</sub>	-	234	-	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
6. Short duration pulse test used to minimize self-heating effect.  
7. Guaranteed by design. Not subject to product testing.

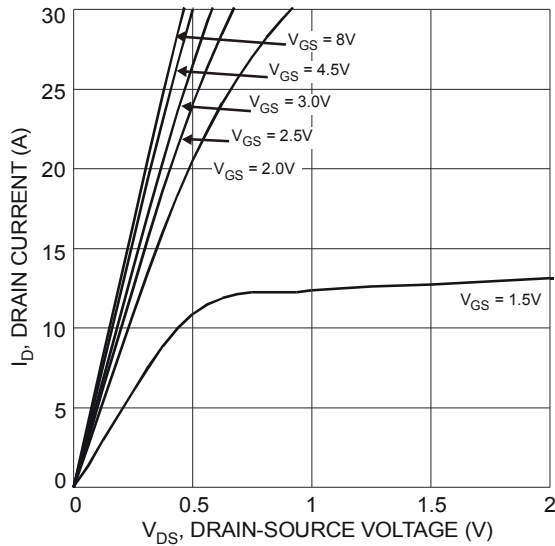


Fig. 1 Typical Output Characteristic

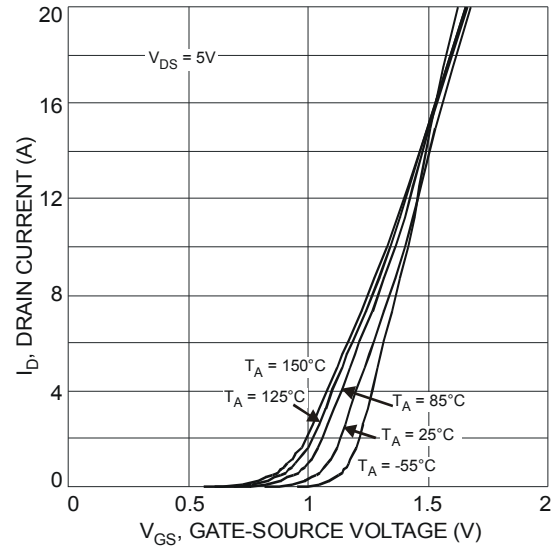


Fig. 2 Typical Transfer Characteristic

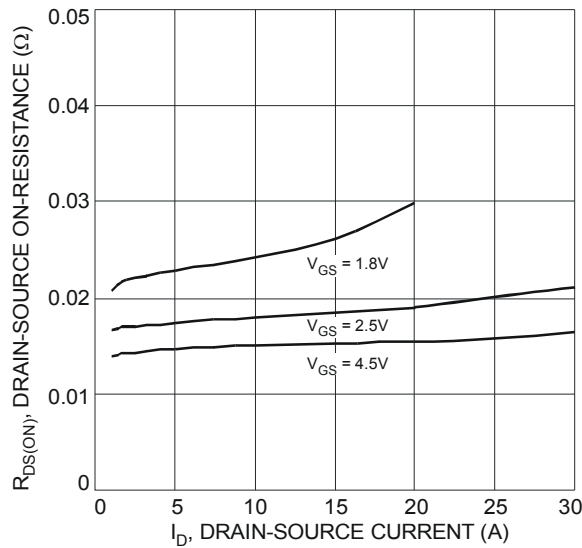


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

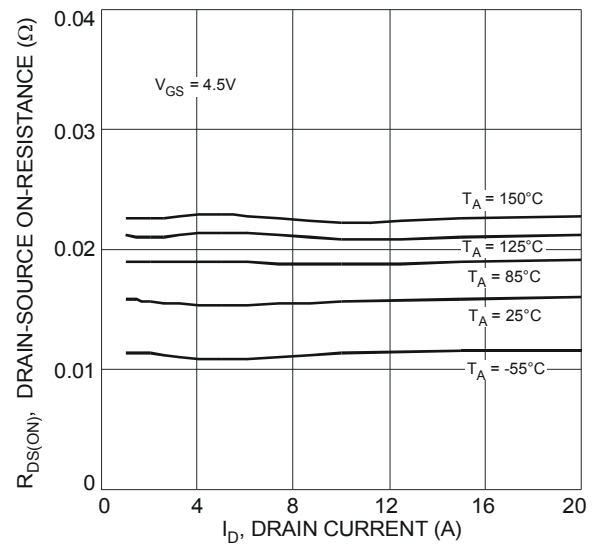


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

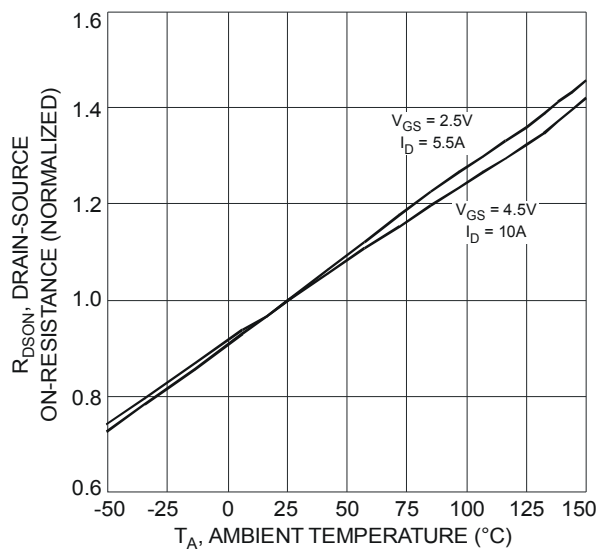


Fig. 5 On-Resistance Variation with Temperature

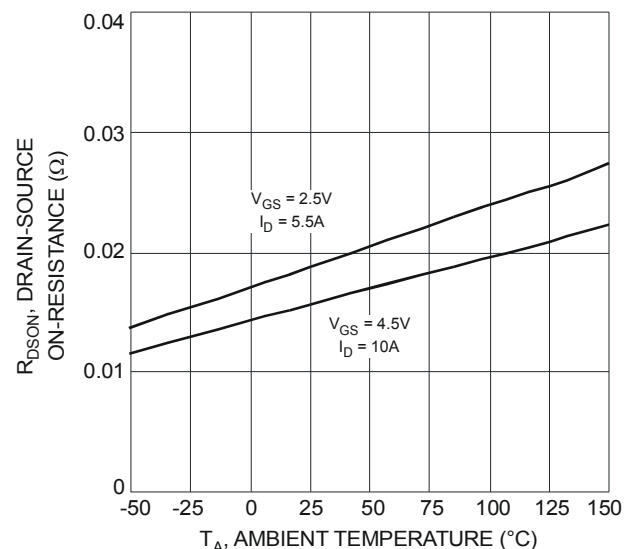


Fig. 6 On-Resistance Variation with Temperature

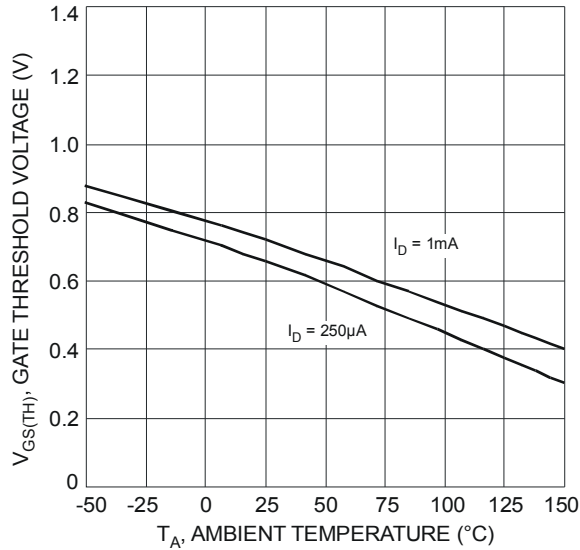


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

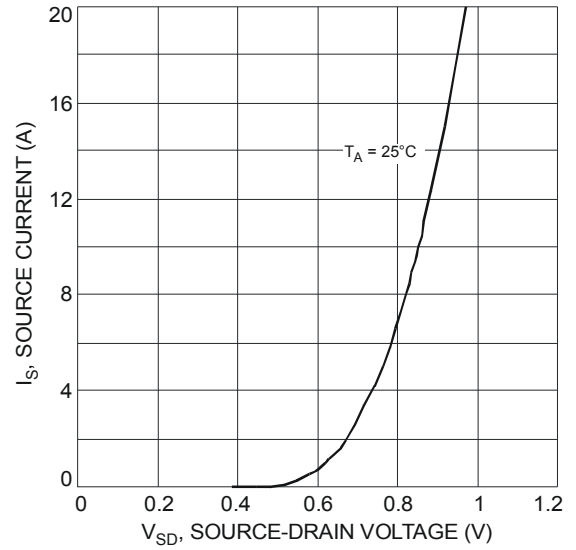


Fig. 8 Diode Forward Voltage vs. Current

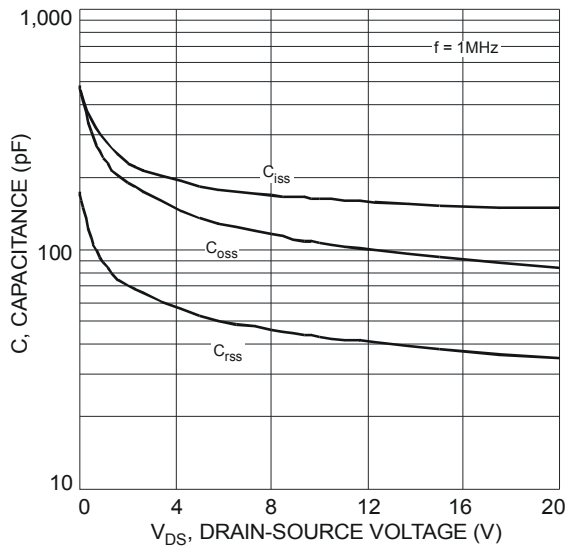


Fig. 9 Typical Total Capacitance

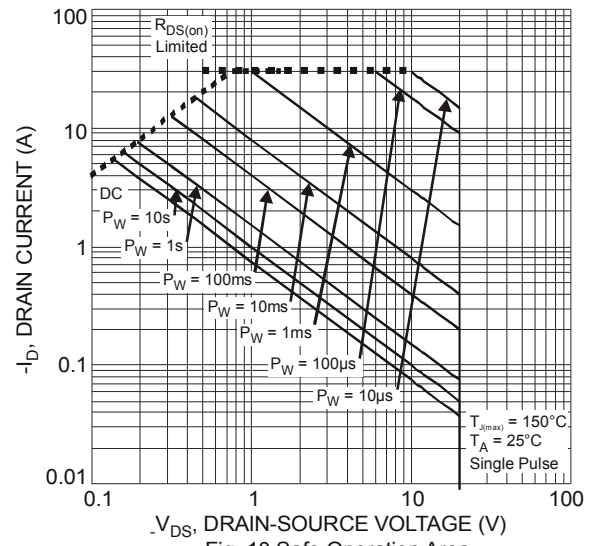


Fig. 10 Safe Operation Area

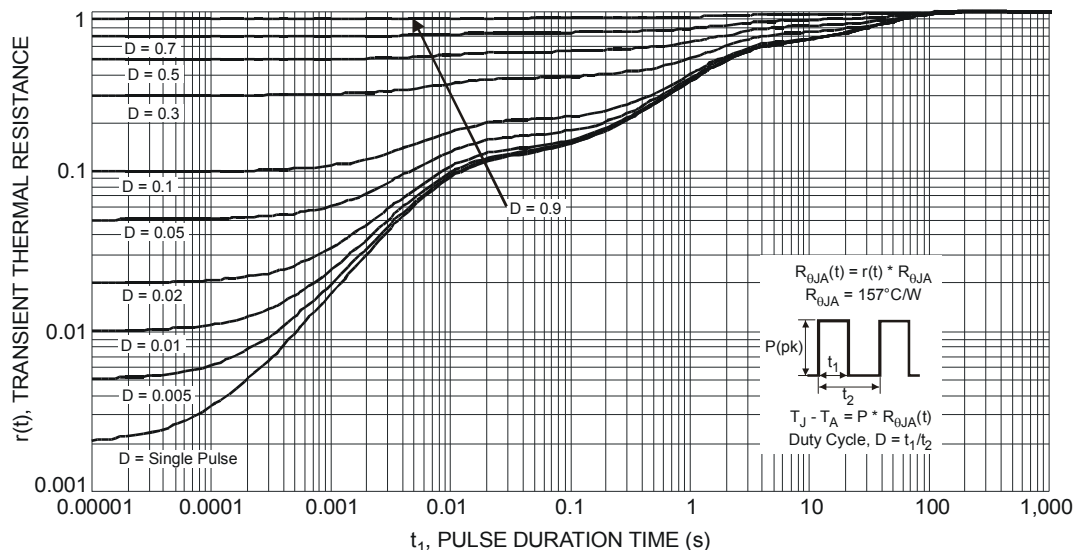
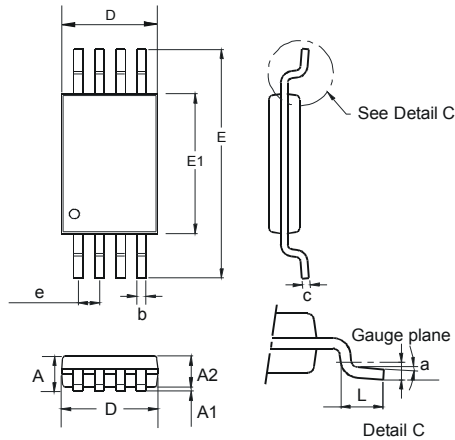


Fig. 11 Transient Thermal Response

## Package Outline Dimensions

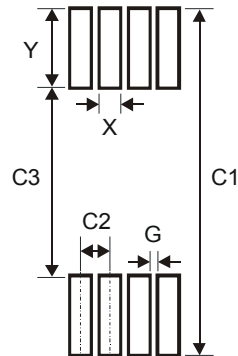
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



TSSOP-8			
Dim	Min	Max	Typ
a	0.09	—	—
A	—	1.20	—
A1	0.05	0.15	—
A2	0.825	1.025	0.925
b	0.19	0.30	—
c	0.09	0.20	—
D	2.90	3.10	3.025
e	—	—	0.65
E	—	—	6.40
E1	4.30	4.50	4.425
L	0.45	0.75	0.60
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.45
Y	1.78
C1	7.72
C2	0.65
C3	4.16
G	0.20

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